Table 2

	CCD44V1		CCD44UV1	
	Parallel CTE	Serial CTE	Parallel CTE	Serial CTE
Pre-radiation				
-80C, Channel A	0.999996	0.999998	0.999996	0.999998
-80C, Channel B	0.999996	0.999998	0.999996	0.999998
-90C, Channel A	0.999997	0.999998	0.999997	0.999998
-90C, Channel B	0.999997	0.999998	0.999997	0.999998
-100C, Channel A	0.999997	0.999999	0.999997	0.999999
-100C, Channel B	0.999997	0.999999	0.999997	0.999999
Post-radiation				
-80C, Channel A	0.999947	0.999994	0.999932	0.999987
-80C, Channel B	0.999949	0.999993	0.999933	0.999985
-90C, Channel A	0.999961	0.999990	0.999942	0.999989
-90C, Channel B	0.999959	0.999987	0.999942	0.999982
-100C, Channel A	0.999977	0.999995	0.999958	0.999993

-100C, Channel B	0.999977	0.999993	0.999954	0.999989
Gain for Channel A		**3.83**		**3.51**
Gain for Channel B		**3.72**		**3.85**

Average value for Parallel CTE taken at Delta Time = 50 Seconds.
Average value for Serial CTE taken for entire data set.

Table 2. Summary of Charge Transfer Efficiency for both devices and for pre- and post-radiation data for both channels A and B.